14000–18000 MHz GaN MMIC Power Amplifier Die

LCI-PA-14000-18000-PS37p5T is a GaN MMIC power amplifier supplied as bare die for 14000–18000 MHz. It supports pulsed operation.

PSAT: 37 dBm (minimum) / 37.5 dBm (typical); Power gain: 15 dB (minimum) / 15.5 dB (typical); PAE: 35 % (typical). Die dimensions: 1.5 × 1 × 0.1 mm.



RF characteristics

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	14000	-	18000	MHz
Saturated output power	Psat	37	37.5	-	dBm
Power gain	Gp	15	15.5	-	dB
Power-gain flatness	ΔGp	-	-	±0.4	dB
Power-added efficiency	PAE	-	35	-	%
Small-signal gain	S21	-	25	26	dB
Small-signal gain flatness	ΔS21	-	-	±1	dB
Input VSWR	VSWR(in)	-	1.6	2	-

DC bias and current

TA = +25 °C

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Drain voltage	Vd	-	28	32	V
Gate voltage	Vg	-3.4	-2.6	-2.4	V
Quiescent drain current	Id	-	0.2	-	A
Dynamic drain current	Idd	-	0.6	0.65	A
Dynamic gate current	Igg	-	0.2	1	mA

Absolute limits

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	Vd	-	-	36	V
Minimum gate bias	Vg	-5	-	-	V
Maximum input power	Pin	-	-	28	dBm
Storage temperature	TSTG	-65	-	150	°C
Maximum channel temperature	Top	-	-	225	°C

Die dimensions

Parameter	Value	Unit
Die dimensions	1.5 × 1 × 0.1	mm

Current publication record · 1.7 · 2026-11-12. Product description or editorial content updated. Replaces revision 1.6.

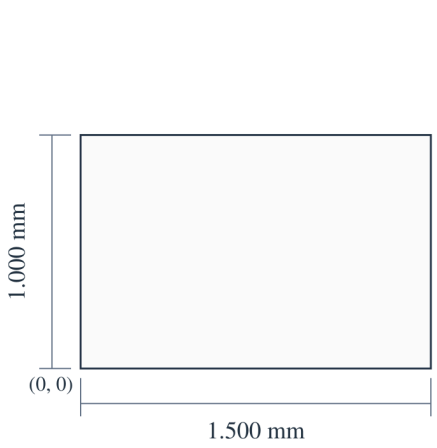
Die integration and bias sequencing

Integrated DC blocking: RFin / RFout. Separate characterization: Vd = +28 V; Vg = -2.6 V. Apply gate bias before drain bias. Remove drain bias before gate bias.

Mechanical Outline

Outline and dimensioned coordinates in mm. Use this drawing as a dimensional reference. Fabrication and wire bonding require complete drawings.

LCI-PA-14000-18000-PS37p5T



X (mm)
Vg: 0.120
Vd1: 0.830
Vd2: 1.400

Y (mm)
RFin / RFout: 0.270

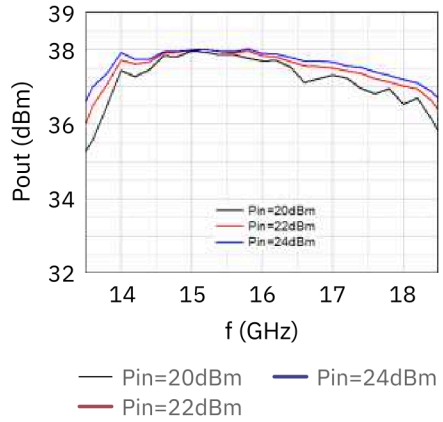
1.500 × 1.000 × 0.100 mm
X, Y: ±0.100 mm
X → · Y ↑ · X, Y: mm

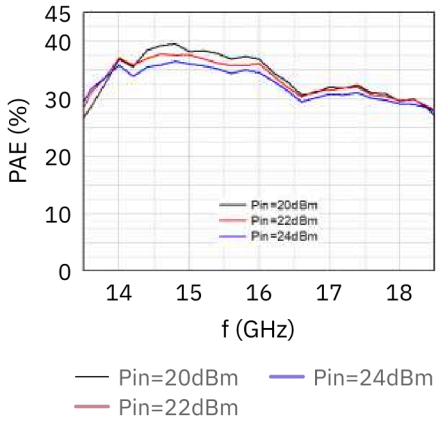
Performance curves

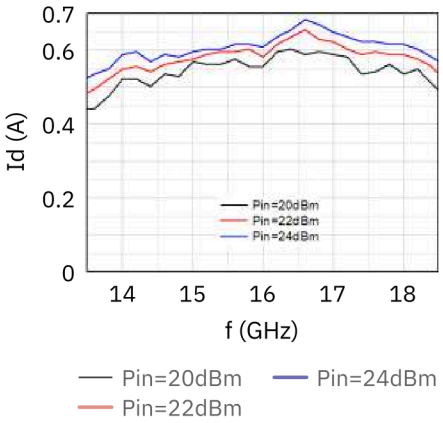
Each performance plot applies to its stated operating conditions.

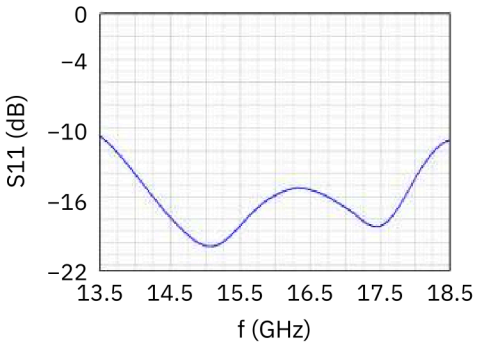
Output power; Power-added efficiency; Drain current; Small-signal gain; Input matching.

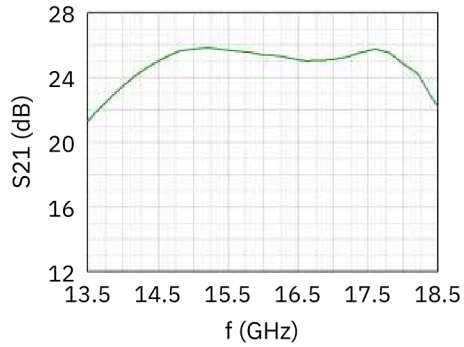
Figure notes: Vd=+28V; Vg=-2.6V. (1–3): Pin = 20 / 22 / 24 dBm; S11 / S21: 13.5–18.5 GHz. Conditions apply to the indicated plots and their own legends.











Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.